



LOW CURRENT, LOW NOISE

# Monolithic Amplifier Die

## TSY-173LN-D+

Mini-Circuits

50Ω 13.5 to 17 GHz

### THE BIG DEAL

- Positive Gain Slope
- Shutdown Feature
- Excellent Noise Figure, 1.2dB Typ.
- Built-In ESD Protection Circuits (Class 1C)
- Low Current Operation, 13.2mA

### APPLICATIONS

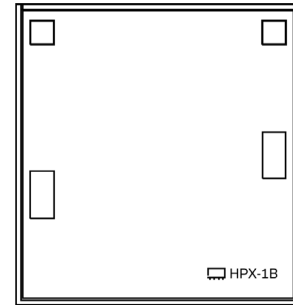
- Point to Point ODU System
- Fixed Satellite
- Radio Location
- Mobile

### PRODUCT OVERVIEW

The TSY-173LN-D+ is a GaAs E-PHEMT based low noise MMIC Amplifier Die with shutdown feature that comes with a unique combination of low noise (1.2dB Typ.) and Low Current (13.2mA Typ.) It is suitable for receiver application. This design operates on a single supply of 3V and is well-matched to 50Ω.

### KEY FEATURES

Feature	Advantages
Low Noise, 1.2dB Typical from 13.5-17GHz	It is a good candidate to be used as the first stage amplifier of the receiver. It provides signal amplification and contributes to the low noise figure of the overall receiver system.
Positive Gain Slope Vs. Frequency <ul style="list-style-type: none"> <li>• +0.6dB/GHz from 13.5 GHz to 15 GHz</li> <li>• +0.4dB/GHz from 15 GHz to 17 GHz</li> </ul>	Useful for compensating for the negative gain slope nature of most wideband microwave components and reducing the need for equalization.
Shutdown Feature	Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage.
Integrated DC Blocks and Bias-Tee	DC Blocks and Bias-Tee have already embedded into the die design. It waives extra effort from the customers to do the external Component design.
Unpackaged Die	Enables user to integrate it directly into hybrids



#### +RoHS Compliant

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

SEE ORDERING INFORMATION ON THE LAST PAGE

REV. OR  
 ECO-011904  
 TSY-173LN-D+  
 MCLNY  
 220214





LOW CURRENT, LOW NOISE

# Monolithic Amplifier Die

TSY-173LN-D+

Mini-Circuits

## ELECTRICAL SPECIFICATIONS<sup>1</sup> AT 25°C, 50Ω, UNLESS NOTED OTHERWISE

Parameter	Condition(GHz)	Amplifier - ON			Amplifier- OFF	Units
		Min	Typ	Max	Typ	
Frequency Range		13.5		17	13.5-17	GHz
Noise Figure	13.5		1.2		---	dB
	14		1.2		---	
	15		1.1		---	
	16		1.2		---	
	17		1.2		---	
Gain	13.5		15.6		-14.8	dB
	14		16		-14.7	
	15		16.5		-15.1	
	16		16.8		-15.6	
	17		16.7		-16.7	
Input Return Loss	13.5		16.4		2.6	dB
	14		18.9		2.7	
	15		18.8		3.1	
	16		15.4		3.3	
	17		16.6		3.2	
Output Return Loss	13.5		11.7		8.8	dB
	14		14.9		8.0	
	15		21.4		6.0	
	16		20.3		5.9	
	17		16		5.2	
P1dB (AMP-ON)	13.5		9.3		---	dBm
	14		9.4		---	
	15		8.7		---	
	16		8.4		---	
	17		6.6		---	
Output IP3 (Pout = -10dBm/Tone)	13.5		22.4		---	dBm
	14		22.9		---	
	15		24.2		---	
	16		21.9		---	
	17		21		---	
Device Operating Voltage (VDD)		2.75	3	3.25	3	V
Device Operating Current(IDD)			13.2	19	0.00012	mA
Control Voltage (VC)		2.25	2.5	2.75	0	V
Control Current(IC)			0.56		0	mA
DC Current (IDD) Variation Vs. Temperature <sup>2</sup>			11.54		---	uA/°C
DC Current (IDD) Variation Vs. Voltage <sup>3</sup>			0.014		---	mA/mV
Thermal Resistance			106.7		---	°C/W

1. Measured on Mini-Circuits Characterization Test Board. Die is packaged in 2x2 mm 6L MCLP and soldered on TB-TSY-173LN+ (See Figure 1)

2. Current Variation vs. Temperature = (Current at 85°C - Current at -45°C) / 130 °C

3. Current Variation vs. Voltage = (Current(mA) at 3.25V - Current (mA) at 2.75V)/((3.25V-2.75V)\*1000mA/mV)





LOW CURRENT, LOW NOISE

# Monolithic Amplifier Die

TSY-173LN-D+

## MAXIMUM RATINGS<sup>4</sup>

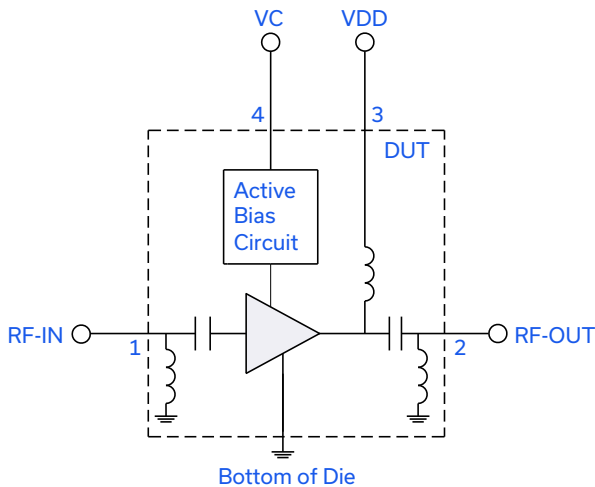
Parameter	Ratings
Operating temperature (ground lead)	-40°C to 85°C
Storage temperature	-65°C to 150°C
Junction Temperature	130°C
Total power dissipation	0.42W
Input power (CW)	+22 dBm
DC voltage at VC	3V
DC voltage at VDD	8V

4. Permanent damage may occur if any of those limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

## TRUTH TABLE + SWITCHING TIME SPECIFICATION

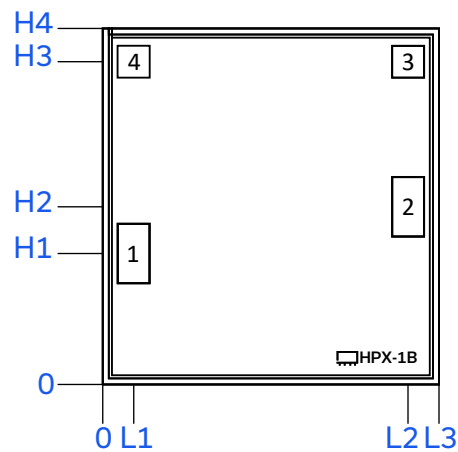
Truth Table		VC Min.	VC Typ.	VC Max.	Units
Amplifier- ON		2.25	2.5	2.75	V
Amplifier -OFF			0	0.2	V
Switching Time Parameter		Min.	Typ.	Max.	Units
Amplifier ON to OFF	OFF Time (50% Control to 10% RF)		13.7		ns
	FALL Time (90% RF to 10% RF)		8.8		ns
Amplifier OFF to ON	ON Time (50% Control to 90% RF)		52.4		ns
	RISE Time (10% RF to 90% RF)		38.8		ns
Control Voltage Leakage (Rising Edge)			0.64		mV
Control Voltage Leakage (Falling Edge)			1.45		mV

## SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION



Pad Number	Description
1	RF-IN
2	RF-OUT
3	VDD
4	VC

## BONDING PAD POSITION



Dimension in  $\mu\text{m}$

L1	L2	L3	H1	H2	H3	H4
78.0	772	850	331.0	449.0	816	900

Thickness	Die size	Pad size 1 & 2	Pad size 3 & 4
100	850 x 900	69 x 139	69 x 69





LOW CURRENT, LOW NOISE

# Monolithic Amplifier Die

TSY-173LN-D+

## CHARACTERIZATION, APPLICATION CIRCUIT

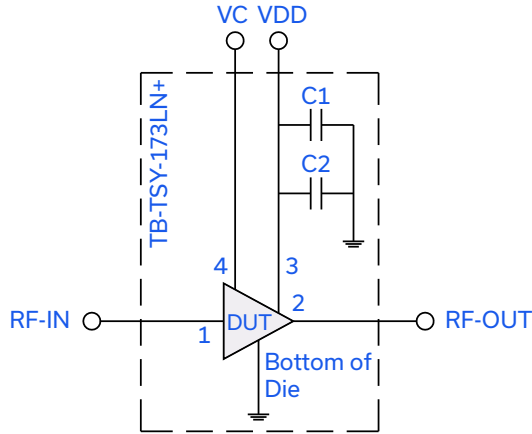


Fig 1. Application and Characterization Circuit

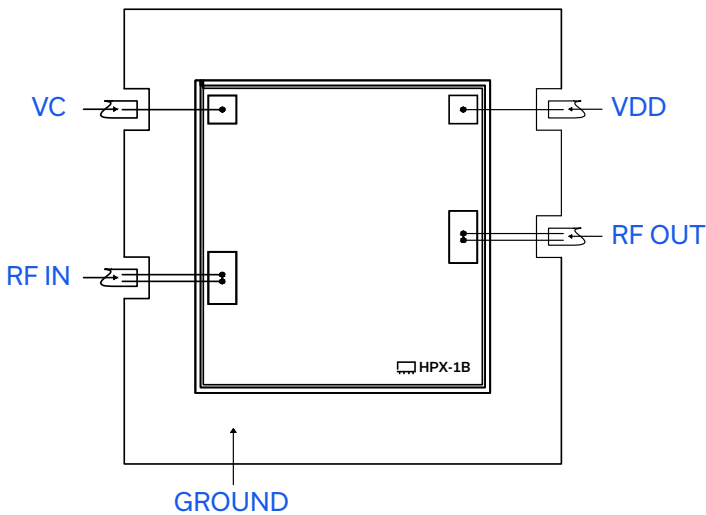
Note: This block diagram is used for application and characterization. (The die is packaged in 2x2mm 6L MCLP and soldered on TB-TSY-173LN+)  
Gain, Return Loss, Output Power at 1dB Compression (P1dB), Output IP3 (OIP3), and Noise Figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:


1. Gain and Return Loss: Pin = -25dBm
2. Output IP3 (OIP3): Two Tones, spaced 1MHz apart, -10dBm/Tone at Output.
3. Switching Time: RF Signal: Pin = -10dBm, fRF = 15GHz ,  
VDD = 3V, VC = Pulse Signal at 100Hz with VHIGH = 2.5V and VLOW = 0V & 50% Duty Cycle.

Component	Size	Value	Part Number	Manufacturer
C1	0402	0.1uF	GRM155R71C104KA88D	Murata
C2	0402	100pF	GRM1555C1H101JA01D	Murata

## ASSEMBLY DRAWING



## ASSEMBLY PROCEDURE

1. Storage  
Dice should be stored in a dry nitrogen purged desiccators or equivalent.
2. ESD  
 MMIC PHEMT amplifier dice are susceptible to electrostatic and mechanical damage. Dice are supplied in antistatic protected material, which should be opened in clean room conditions at an appropriately grounded anti-static workstation.
3. Die Handling and Attachment  
Devices need careful handling using correctly designed collets, it is recommended to handle the chip along the edges with a custom design collet. The die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are Ablestik 84-1 LMISR4 or equivalents. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition.
5. Wire Bonding  
Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the dice gold bond pads. Thermo-sonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1mil diameter. Bonds must be made from the bond pads on the die to the packaged or substrate. All bond wires should be kept as short as low as reasonable to minimize performance degradation due to undesirable series inductance.





All Mini-Circuits products are manufactured under exacting quality assurance and control standards, and are capable of meeting published specifications after being subjected to any or all of the following physical and environmental test.

Specification	Test/Inspection Condition	Reference/Spec
Operating Temperature	-40° to 85° C or -40° to 105° C or -55° to 105° C or -45° to 105° C Ambient Environment	Refer to Individual Model Data Sheet
Storage Environment (Die)	-65° to 150°C	Individual Model Data Sheet
Storage Environment(Packaging)	-40° to 70°C and 40 to 60% humidity (In Factory Shipped Package)	